



# FFSD10120A

## Silicon Carbide Schottky Diode

### 1200 V, 10 A

#### Features

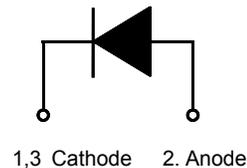
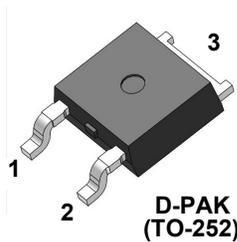
- Max Junction Temperature 175 °C
- Avalanche Rated 100 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

#### Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

#### Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.



#### Absolute Maximum Ratings $T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FFSD10120A	Unit	
$V_{RRM}$	Peak Repetitive Reverse Voltage	1200	V	
$E_{AS}$	Single Pulse Avalanche Energy (Note 1)	100	mJ	
$I_F$	Continuous Rectified Forward Current @ $T_C < 164\text{ }^\circ\text{C}$	10	A	
	Continuous Rectified Forward Current @ $T_C < 135\text{ }^\circ\text{C}$	22		
$I_{F, Max}$	Non-Repetitive Peak Forward Surge Current	$T_C = 25\text{ }^\circ\text{C}$ , 10 $\mu\text{s}$	850	A
		$T_C = 150\text{ }^\circ\text{C}$ , 10 $\mu\text{s}$	800	A
$I_{F, SM}$	Non-Repetitive Forward Surge Current	Half-Sine Pulse, $t_p = 8.3\text{ ms}$	90	A
$I_{F, RM}$	Repetitive Forward Surge Current	Half-Sine Pulse, $t_p = 8.3\text{ ms}$	35	A
$P_{tot}$	Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	283	W
		$T_C = 150\text{ }^\circ\text{C}$	47	W
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$	

#### Thermal Characteristic

Symbol	Parameter	FFSD10120A	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.53	$^\circ\text{C/W}$

### Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSD10120A	FFSD10120A	D-PAK	N/A	13"	N/A	2500 units

### Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_F$	Forward Voltage	$I_F = 10\text{ A}, T_C = 25^\circ\text{C}$	-	1.45	1.75	V
		$I_F = 10\text{ A}, T_C = 125^\circ\text{C}$	-	1.7	2	
		$I_F = 10\text{ A}, T_C = 175^\circ\text{C}$	-	2	2.4	
$I_R$	Reverse Current	$V_R = 1200\text{ V}, T_C = 25^\circ\text{C}$	-	-	200	$\mu\text{A}$
		$V_R = 1200\text{ V}, T_C = 125^\circ\text{C}$	-	-	300	
		$V_R = 1200\text{ V}, T_C = 175^\circ\text{C}$	-	-	400	
$Q_C$	Total Capacitive Charge	$V = 800\text{ V}$	-	62	-	nC
C	Total Capacitance	$V_R = 1\text{ V}, f = 100\text{ kHz}$	-	612	-	pF
		$V_R = 400\text{ V}, f = 100\text{ kHz}$	-	58	-	
		$V_R = 800\text{ V}, f = 100\text{ kHz}$	-	47	-	

**Notes:**

1: EAS of 100 mJ is based on starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.5\text{ mH}$ ,  $I_{AS} = 20\text{ A}$ ,  $V = 150\text{ V}$ .

### Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

Figure 1. Forward Characteristics

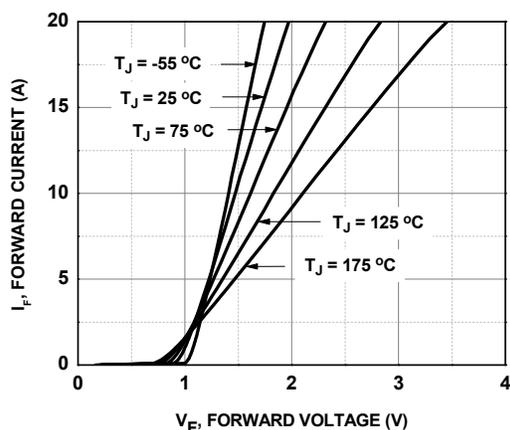


Figure 2. Reverse Characteristics

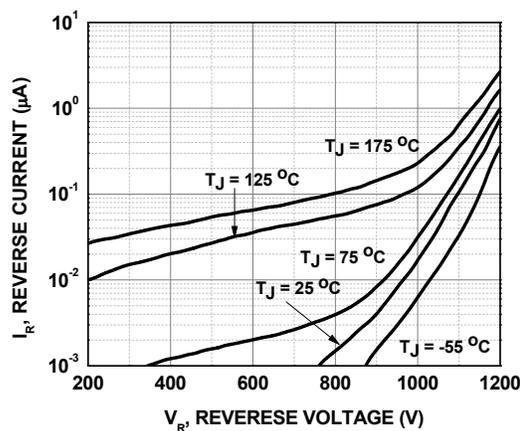


Figure 3. Reverse Characteristics

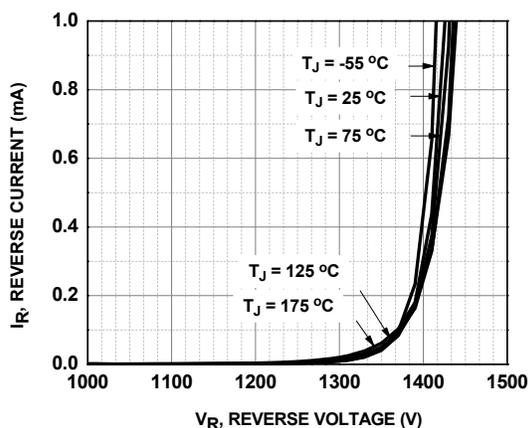
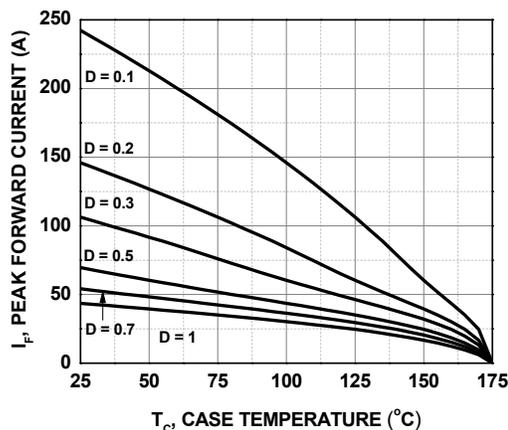


Figure 4. Current Derating



Typical Characteristics  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.

Figure 5. Power Derating

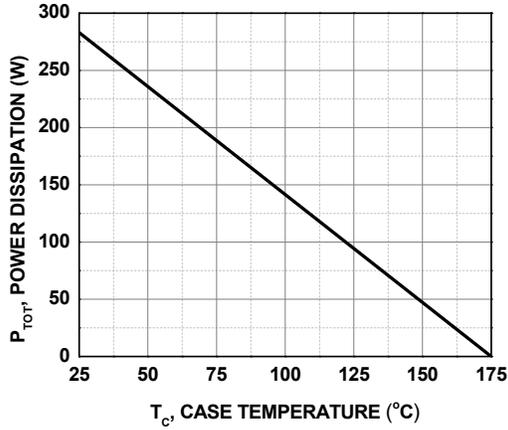


Figure 6. Capacitive Charge vs. Reverse Voltage

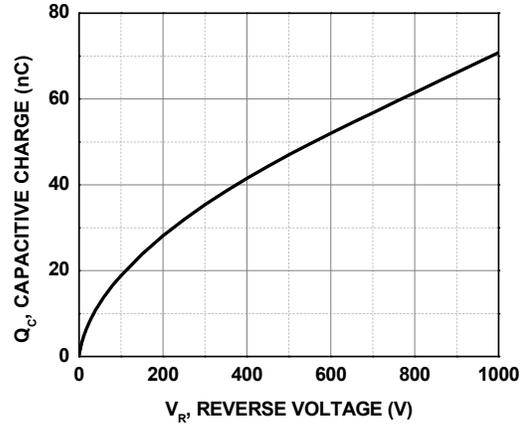


Figure 7. Capacitance vs. Reverse Voltage

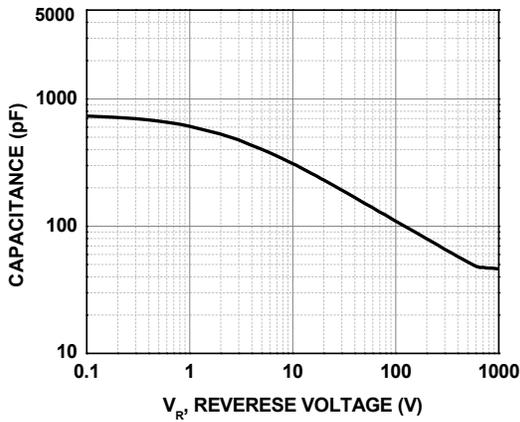


Figure 8. Capacitance Stored Energy

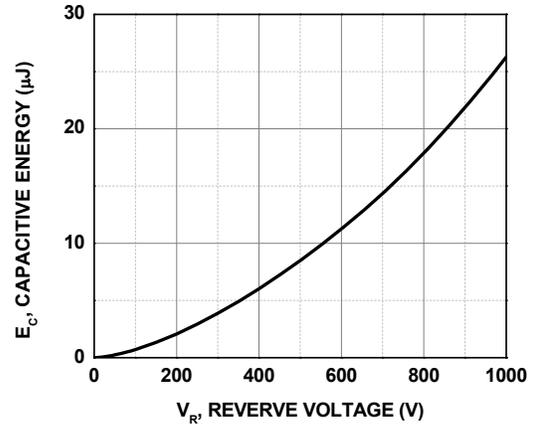
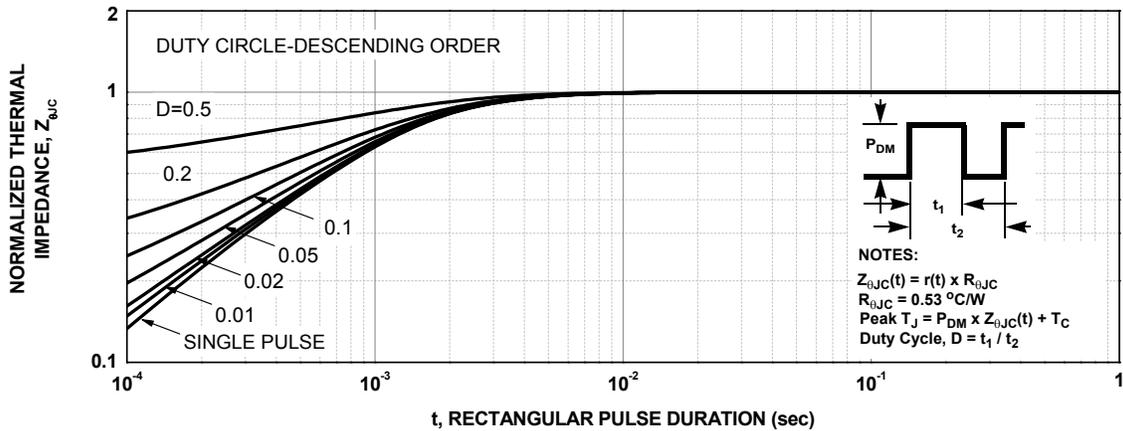


Figure 9. Junction-to-Case Transient Thermal Response Curve



### Test Circuit and Waveforms

Figure 10. Unclamped Inductive Switching Test Circuit & Waveform

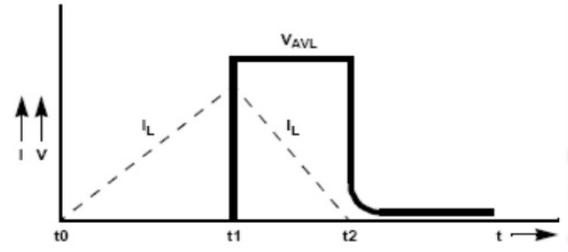
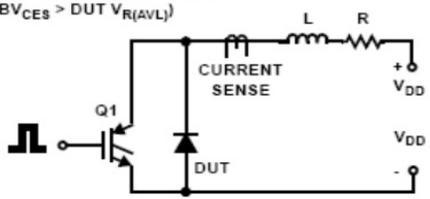
$L = 0.5\text{mH}$

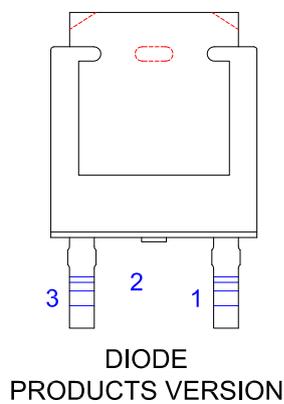
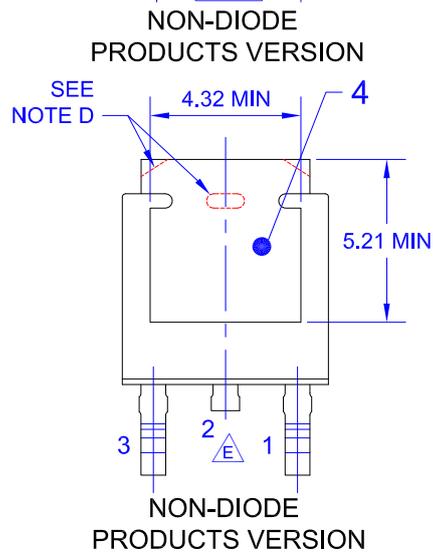
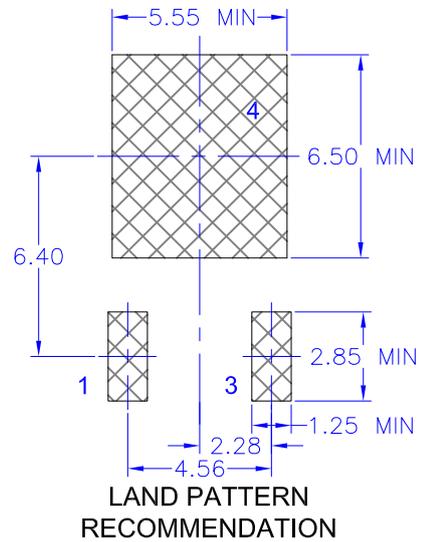
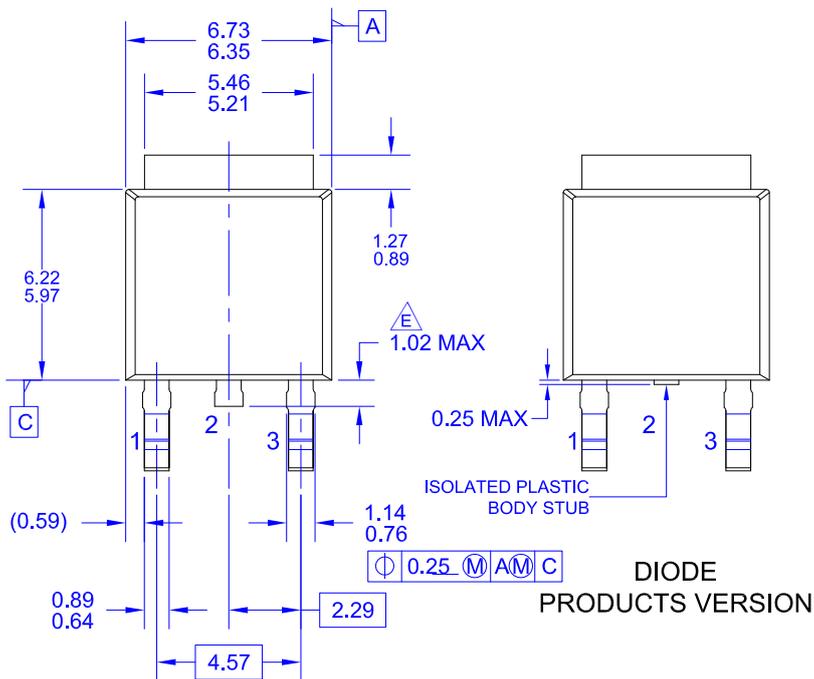
$R < 0.1\Omega$

$V_{DD} = 50\text{V}$

$$E_{AVL} = 1/2 L I^2 [V_{R(AVL)} / (V_{R(AVL)} - V_{DD})]$$

Q1 = IGBT ( $BV_{CES} > DUT V_{R(AVL)}$ )





NOTES: UNLESS OTHERWISE SPECIFIED  
A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.

B) ALL DIMENSIONS ARE IN MILLIMETERS.

C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.

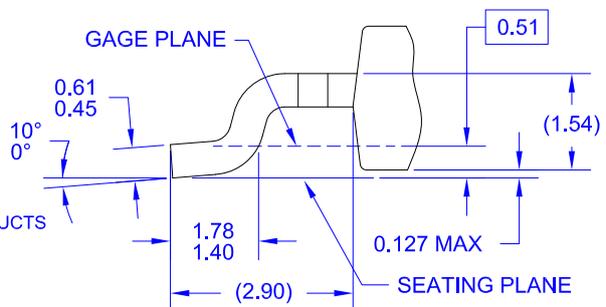
D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.

E) TRIMMED METAL CENTER LEAD IS PRESENT ON FOR NON-DIODE PRODUCTS

F) DIMENSIONS ARE EXCLUSIVE OF BURS, MOLD FLASH AND TIE BAR EXTRUSIONS.

G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.

H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11



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